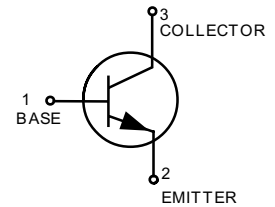
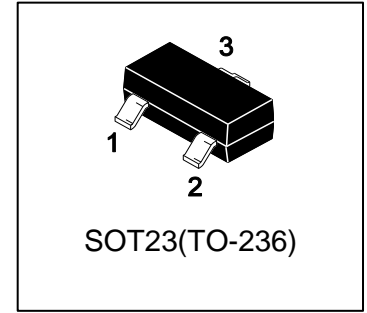


LBC847CLT1G

S-LBC847CLT1G

General Purpose Transistors NPN Silicon



1. FEATURES

- Moisture Sensitivity Level: 1
- ESD Rating – Human Body Model: >4000 V
– Machine Model: >400 V
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBC847CLT1G	1G	3000/Tape&Reel
LBC847CLT3G	1G	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	V _{CEO}	45	V
Collector–Base Voltage	V _{CBO}	50	V
Emitter–Base Voltage	V _{EB0}	6	V
Collector Current — Continuous	I _C	100	mA

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	R _{θJA}	556	°C/W
Junction and Storage temperature	T _J , T _{stg}	-55~+150	°C

1. FR-5 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = 10 mA, IB = 0)	VBR(CEO)	45	-	-	V
Collector–Emitter Breakdown Voltage (IC = 10 μA, VEB = 0)	VBR(CES)	50	-	-	V
Collector–Base Breakdown Voltage (IC = 10 μA, IE= 0)	VBR(CBO)	50	-	-	V
Emitter–Base Breakdown Voltage (IE = 1.0 μA, IC = 0)	VBR(EBO)	6	-	-	V
Collector Cutoff Current (VCB = 30 V) (VCB = 30 V, TA = 150°C)	ICBO	-	-	15 5	nA μA
Collector-Emitter cutoff Current (VCE=45V, IB=0)	ICEO	-	-	10	μA
Emitter-Base cut-off current (VEB=5V, IC =0)	IEBO	-	-	100	nA

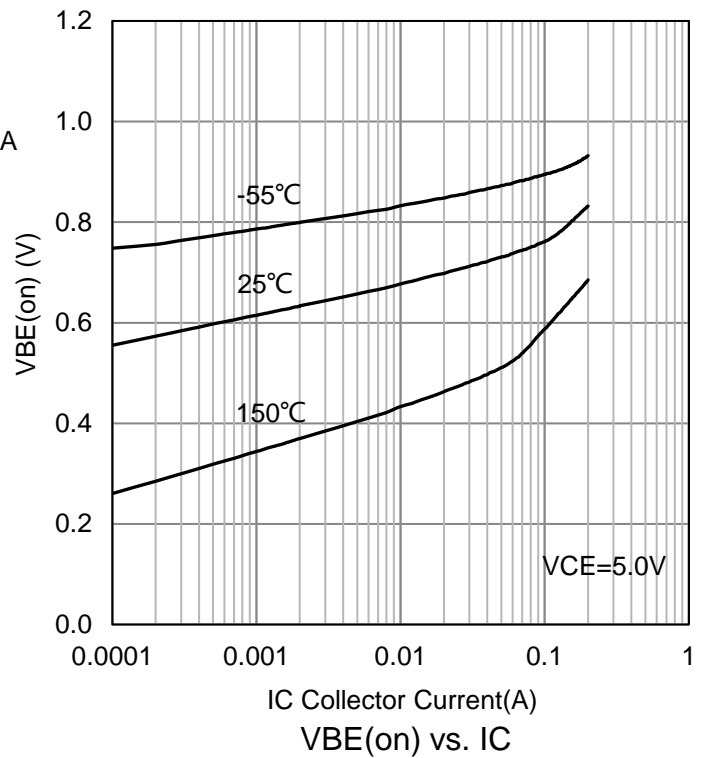
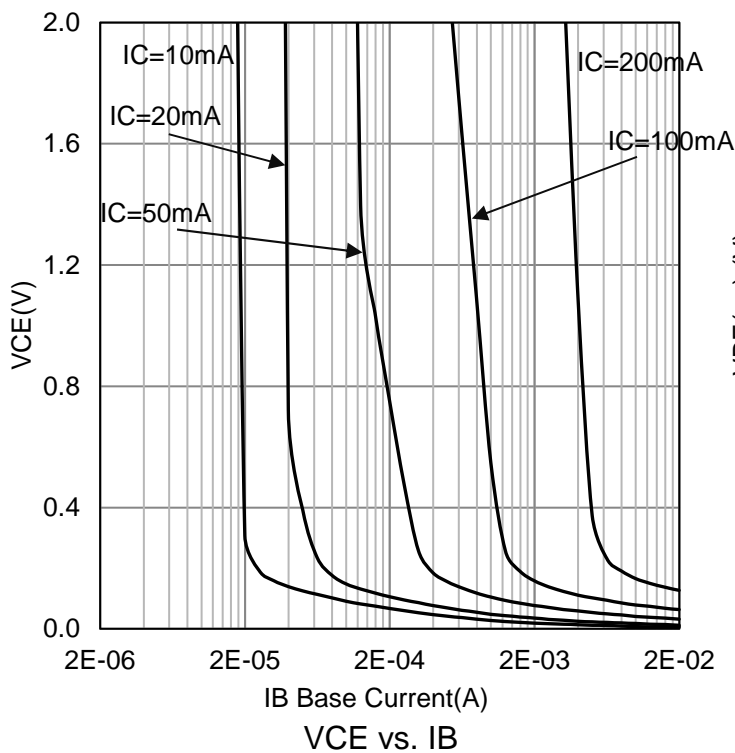
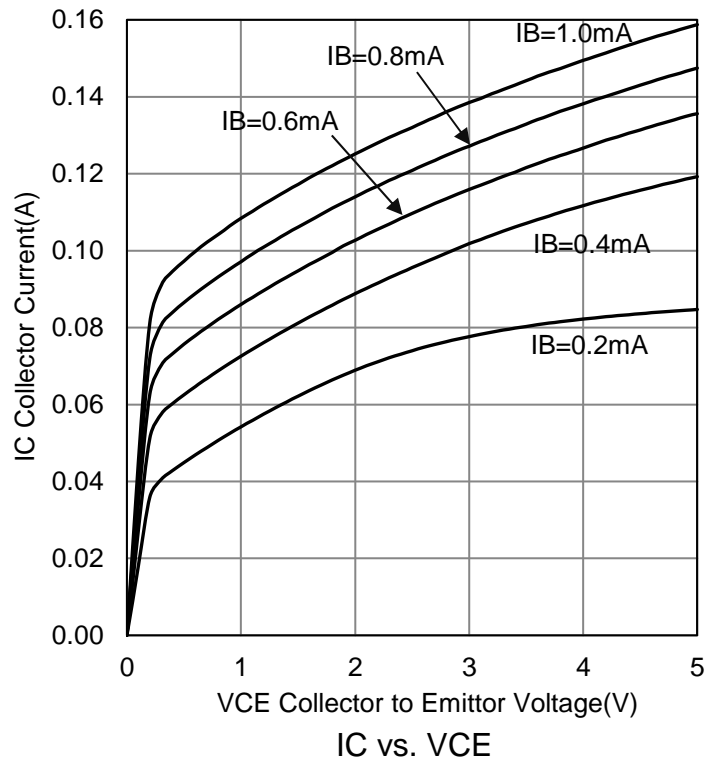
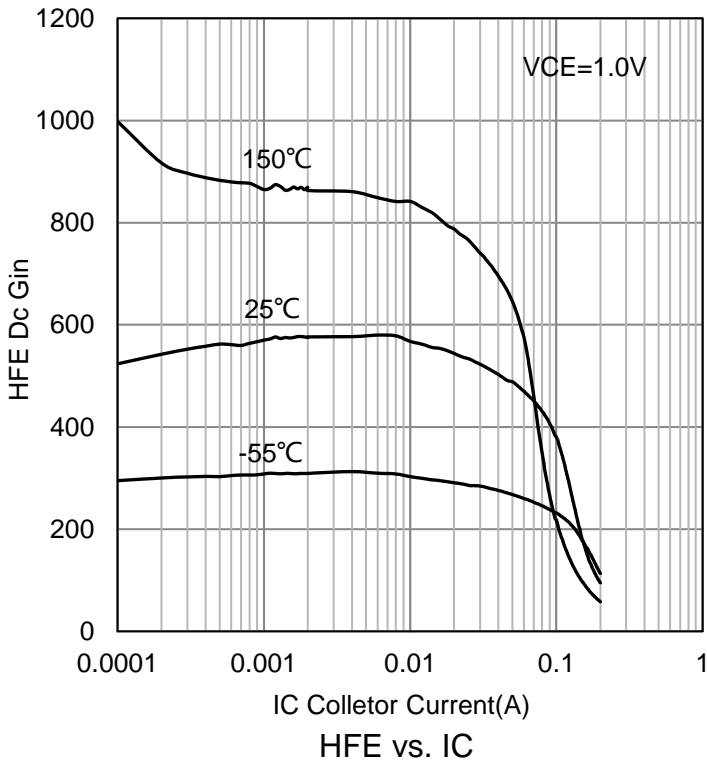
ON CHARACTERISTICS

DC Current Gain (IC = 2.0 mA, VCE = 5.0 V)	HFE	420	520	800	
Collector–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VCE(sat)	-	-	0.25 0.6	V
Base–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VBE(sat)	-	-	0.9 1.2	V
Base–Emitter turn on Voltage (IC = 2.0 mA, VCE = 5.0 V) (IC = 10 mA, VCE = 5.0 V)	VBE(on)	580	660	700 770	mV

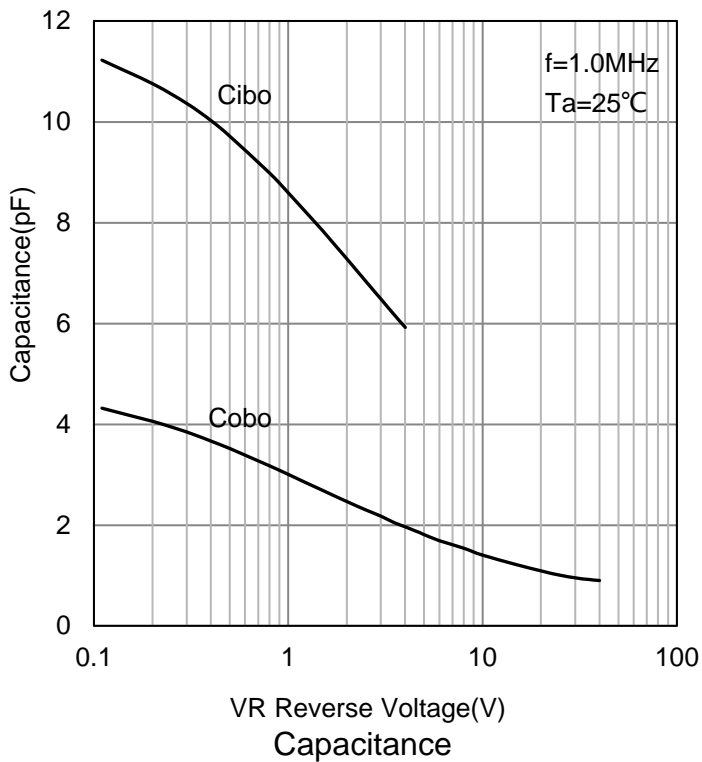
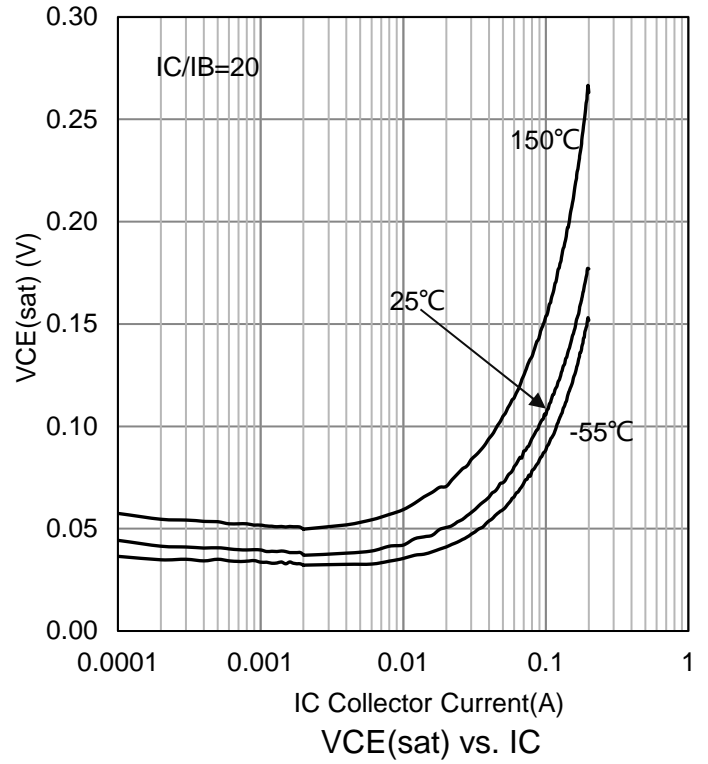
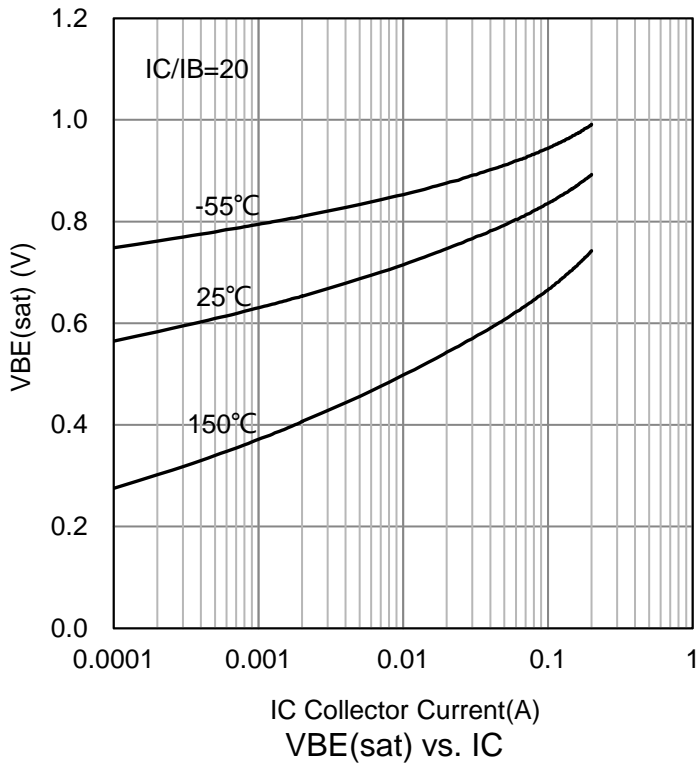
SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (IC = 10 mA, VCE = 5.0 V, f = 100 MHz)	fT	100	-	-	MHz
Output Capacitance (VCB = 10 V, f = 1.0 MHz)	Cobo	-	-	4.5	pF
Noise Figure (IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 kΩ f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB

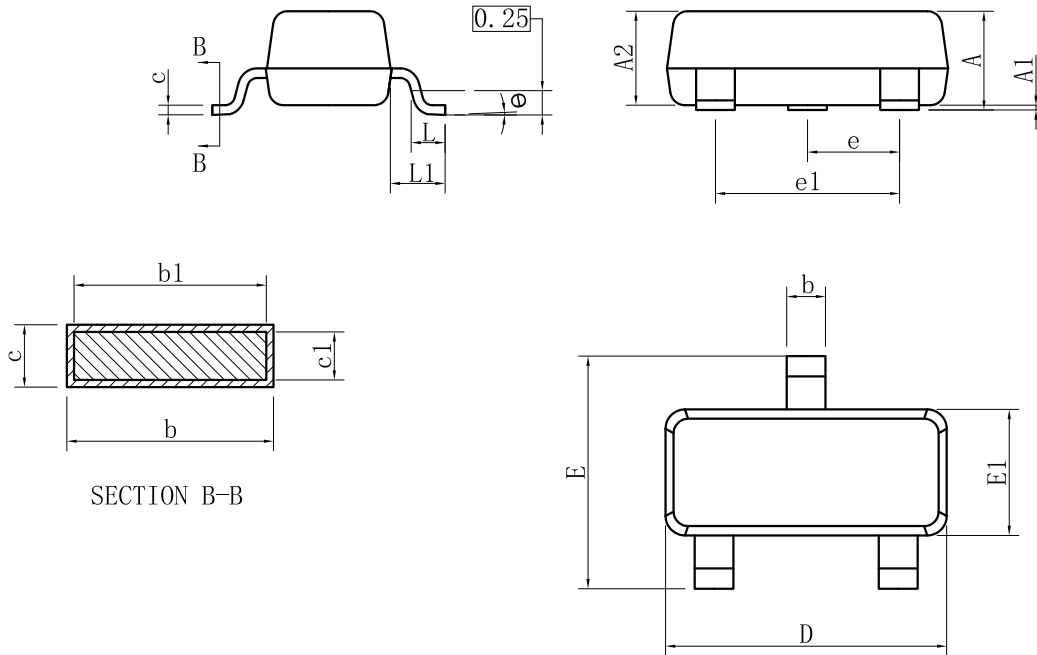
6.ELECTRICAL CHARACTERISTICS CURVES



6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



7.OUTLINE AND DIMENSIONS

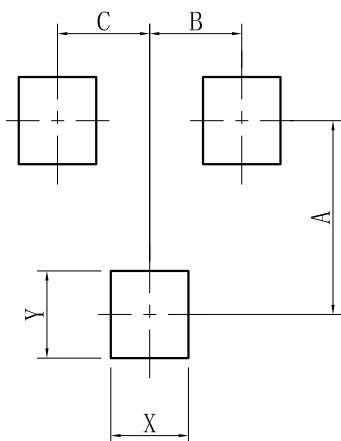


SOT23			
DIM	MIN	NOR	MAX
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.50
b1	0.30	0.40	0.45
c	0.08	-	0.20
c1	0.08	0.10	0.16
D	2.80	2.90	3.04
E	2.10	-	2.64
E1	1.20	1.30	1.40
e	0.95BSC		
e1	1.90BSC		
L	0.40	0.46	0.60
L1	0.54REF		
θ	0°	-	8°
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um

8.SOLDERING FOOTPRINT



SOT-23	
DIM	(mm)
X	0.80
Y	0.90
A	2.00
B	0.95
C	0.95

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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